



CRESTEC e-beam lithography system



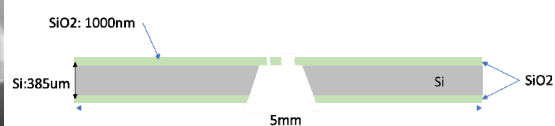
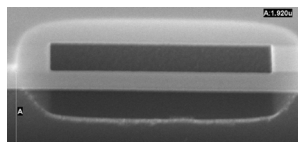
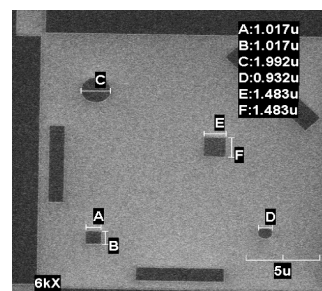
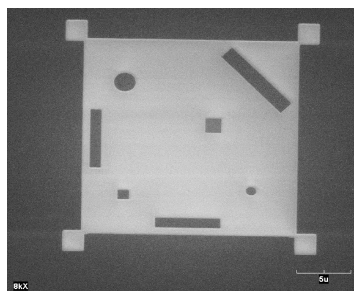
CABL-9000 Series



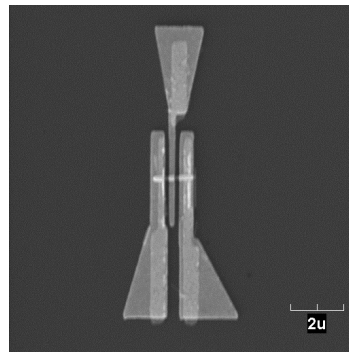
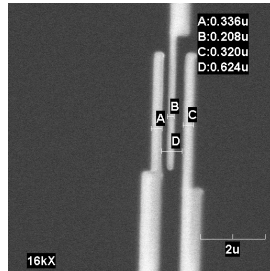
Cavities on a SiO₂ window



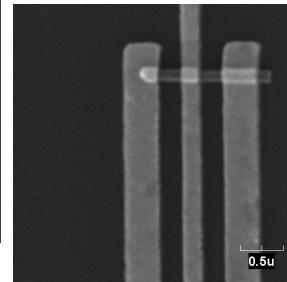
Cavities lateral size $\sim 1\mu\text{m}$ for mechanical testing of 2D flakes



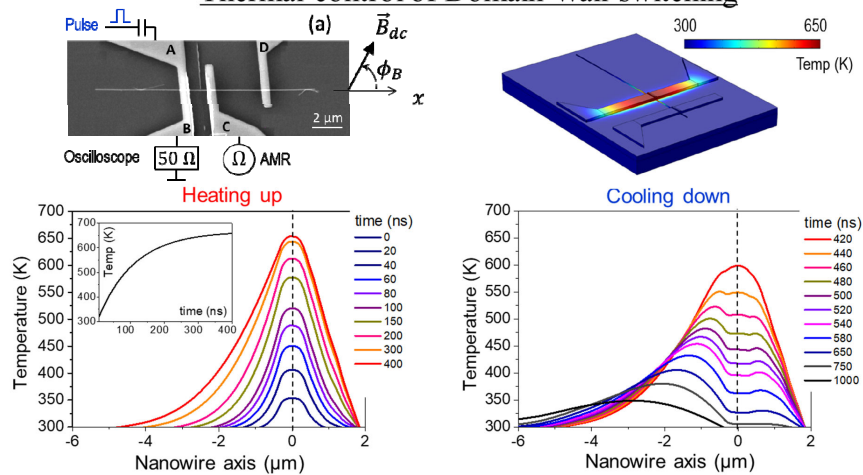
Electrical characterization of single (Ga,Al,In)N Nanowires



Gap ~ 150 nm

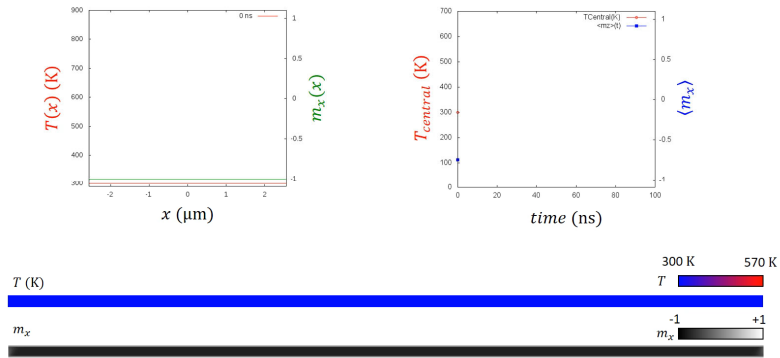


Thermal control of Domain Wall switching



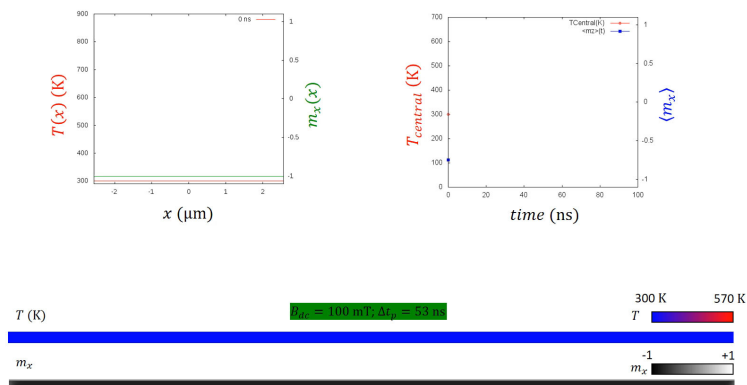
Contacting individual electrodeposited magnetic nanowires

$B_{dc} = 100 \text{ mT}$; $\Delta t_p = 51 \text{ ns}$

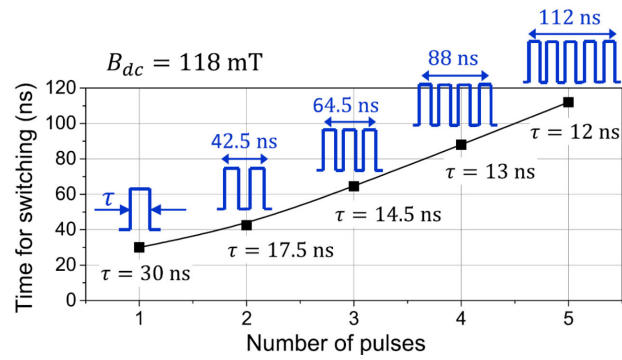


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Contacting individual electrodeposited magnetic nanowires

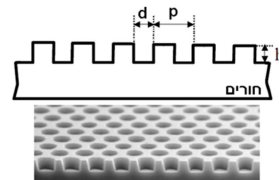


Hexagonal structure on sapphire with holes of diameter d , spacing p and depth h

Picture shows the set-up in SEM chamber.



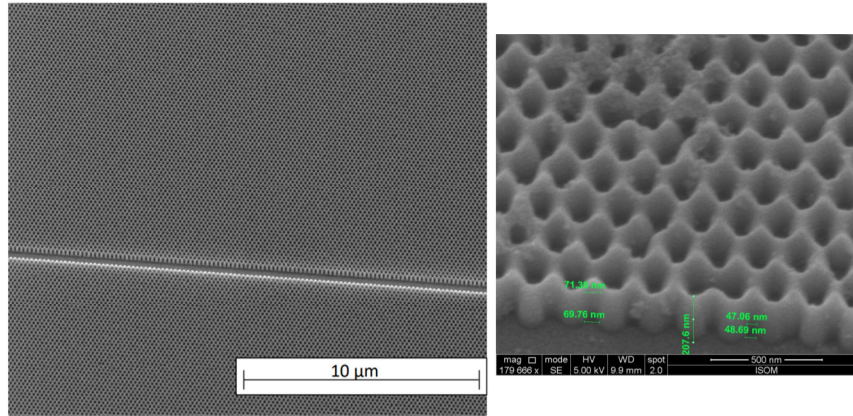
$d \text{ (nm)}$	$p \text{ (nm)}$	$h \text{ (nm)}$
$135 \pm 10\% \text{ (RMS)}$	$175 \pm 10\% \text{ (RMS)}$	$145 \pm 10\% \text{ (RMS)}$



Total Area $6 \times 6 \text{ mm}$

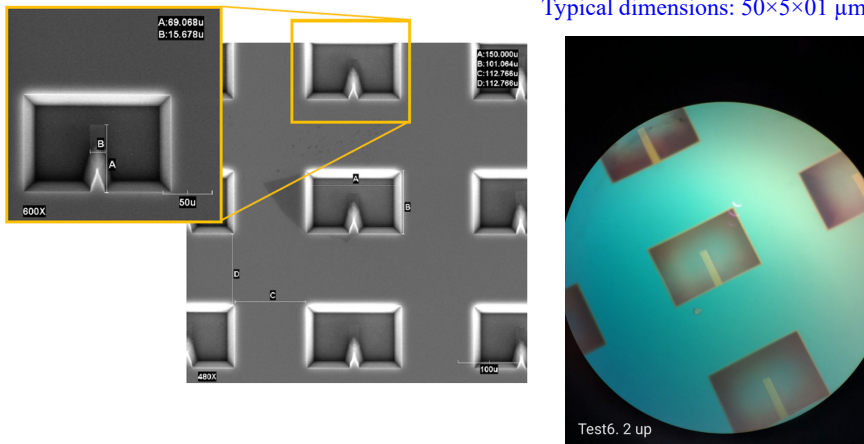
SEM image (tilt angle: 45°)

This SEM image shows a very low number of defects along the device



4.8 × 4.8 mm overall surface. Areas of 100 cantilevers with ultralow stress

Typical dimensions: 50×5×01 µm

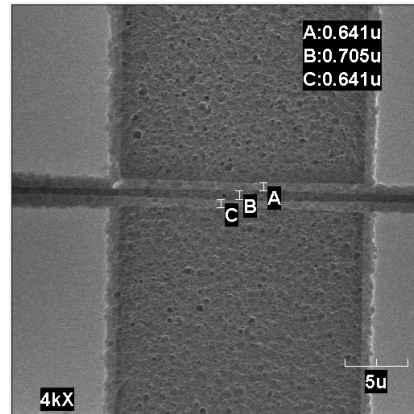
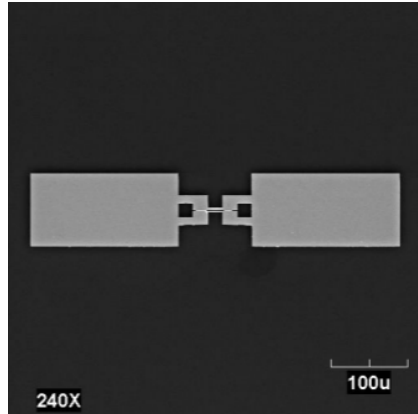




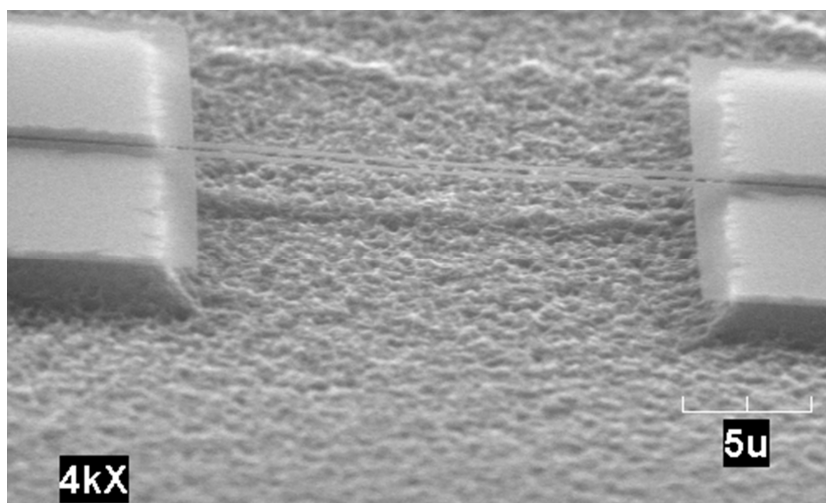
Bridges in $N_3Si_4/Si(100)$



Two parallel bridges 650 nm wide, separated 700 nm



Bridges in $N_3Si_4/Si(100)$



株式会社クレステック 説明会



ISOM



CRESTEC

UPM

- Position Resolution: 18 to 20 bits
- Clock Frequency: 20 to 100 MHz
- Vector (r,theta) circular pattern generation function
- Field size modulation function
- Full upgrade of the software

Available from Jan 2021